# 2SC2463

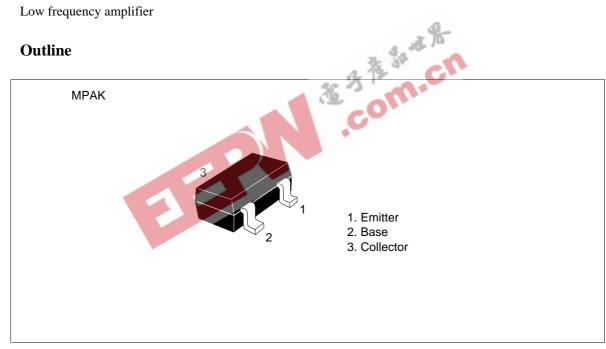
## Silicon NPN Epitaxial

# **HITACHI**

## **Application**

Low frequency amplifier

#### **Outline**





## 2SC2463

## **Absolute Maximum Ratings** (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{\text{CBO}}$	55	V
Collector to emitter voltage	$V_{\text{CEO}}$	50	V
Emitter to base voltage	$V_{EBO}$	5	V
Collector current	I <sub>c</sub>	100	mA
Collector power dissipation	P <sub>c</sub>	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

## **Electrical Characteristics** (Ta = 25°C)

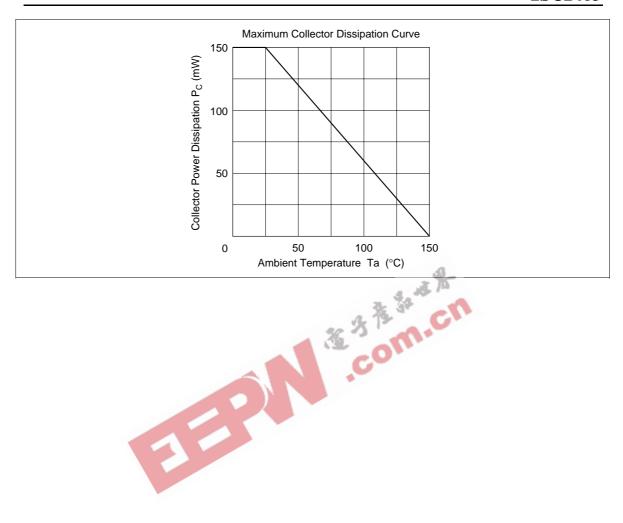
<b>Electrical Characteristics</b> (Ta = 25°C)				A AT The		
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	55	3	25	V	$I_{c} = 10  \mu A,  I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	50	1-	100	V	$I_{c}$ = 1 mA, $R_{BE}$ = $\infty$
Emitter to base breakdown voltage	V <sub>(BR)EBO</sub>	5		_	V	$I_{E} = 10 \ \mu A, \ I_{C} = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	0.5	μΑ	$V_{CB} = 30 \text{ V}, I_{E} = 0$
Emitter cutoff current	I <sub>EBO</sub>	_	_	0.5	μΑ	$V_{EB} = 2 \text{ V}, I_{C} = 0$
DC current transfer ratio	h <sub>FE</sub> *1	250	_	1200		$V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	0.5	V	$I_{\rm C}$ = 10 mA, $I_{\rm B}$ = 1 mA
Base to emitter voltage	$V_{BE}$	_	_	0.75	V	$V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$

Note: 1. The 2SC2463 is grouped by  $h_{\rm FE}$  as follows.

Grade	D	E	F
Mark	DD	DE	DF
h <sub>FE</sub>	250 to 500	400 to 800	600 to 1200

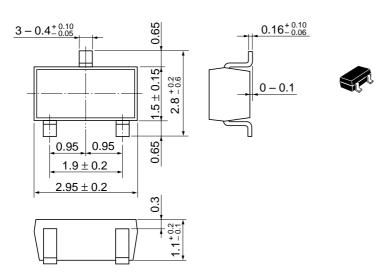
See characteristic curves of 2SC1345.

## 2SC2463





Unit: mm



Hitachi Code	MPAK
JEDEC	_
EIAJ	Conforms
Weight (reference value)	0.011 a

#### **Cautions**

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Semiconductor & Integrated Circuits. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109 URI

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#### For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose,CA 95134 Tel: <1> (408) 433-1990 Fax: <1>(408) 433-0223 Hitachi Europe GmbH Electronic components Group Dornacher Stra§e 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0

Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group.

Whitebrook Park

Lower Cookham Road

Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533

Hitachi Asia Ltd

Taipei Branch Office 3F, Hung Kuo Building. No.167 Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Tsim Sha Tsui, Kowloon, Hong Kong Tel: <852> (2) 735 9218 Fax: <852> (2) 730 0281 Telex: 40815 HITEC HX

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